

# NDS9933A

## Dual P-Channel Enhancement Mode Field Effect Transistor

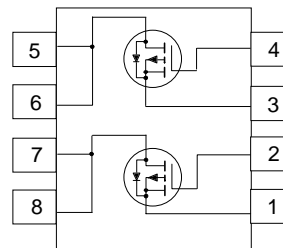
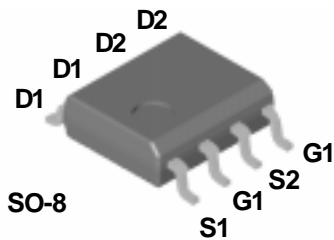
### General Description

This P-Channel enhancement mode power field effect transistor is produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance.

These devices are particularly suited for low voltage applications such as DC motor control and DC/DC conversion where fast switching, low in-line power loss, and resistance to transients are needed.

### Features

- -2.8 A, -20 V.  $R_{DS(on)} = 0.14 \Omega @ V_{GS} = -4.5 V$   
 $R_{DS(on)} = 0.19 \Omega @ V_{GS} = -2.7 V$   
 $R_{DS(on)} = 0.20 \Omega @ V_{GS} = -2.5 V.$
- High density cell design for extremely low  $R_{DS(on)}$
- High power and current handling capability in a widely used surface mount package.
- Dual MOSFET in surface mount package.



### Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	NDS9933A	Units
$V_{DSS}$	Drain-Source Voltage	-20	V
$V_{GSS}$	Gate-Source Voltage	$\pm 8$	V
$I_D$	Drain Current - Continuous (Note 1a)	-2.8	A
		-10	
$P_D$	Power Dissipation for Dual Operation	2	W
	Power Dissipation for Single Operation (Note 1a)	1.6	
	(Note 1b)	1	
	(Note 1c)	0.9	
$T_J, T_{stg}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	78	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	40	$^\circ\text{C/W}$

### Package Outlines and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
NDS9933A	NDS9933A	13"	12mm	2500 units

## Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-20			V
$\frac{BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-25		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 8\text{ V}, V_{DS} = 0\text{ V}$			100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -8\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

### On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.4	-0.65	-1	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		4		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -4.5\text{ V}, I_D = -2.8\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -2.8\text{ A}, T_J = 125^\circ\text{C}$ $V_{GS} = -2.7\text{ V}, I_D = -1.5\text{ A}$ $V_{GS} = -2.5\text{ V}, I_D = -1.5\text{ A}$		0.105 0.150 0.135 0.140	0.140 0.240 0.190 0.200	$\Omega$
$I_{D(on)}$	On-State Drain Current	$V_{GS} = -4.5\text{ V}, V_{DS} = -5\text{ V}$	-10			A
$g_{FS}$	Forward Transconductance	$V_{DS} = -5\text{ V}, I_D = -2.8\text{ A}$		6.5		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		405		pF
$C_{oss}$	Output Capacitance			170		pF
$C_{riss}$	Reverse Transfer Capacitance			45		pF

### Switching Characteristics (Note 2)

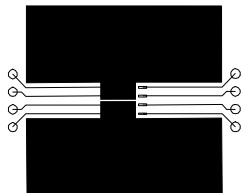
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -5\text{ V}, I_D = -1\text{ A},$ $V_{GS} = -4.5\text{ V}, R_{GEN} = 6\ \Omega$		6.5	13	ns
$t_r$	Turn-On Rise Time			20	35	ns
$t_{d(off)}$	Turn-Off Delay Time			31	50	ns
$t_f$	Turn-Off Fall Time			21	35	ns
$Q_g$	Total Gate Charge	$V_{DS} = -5\text{ V}, I_D = -2.8\text{ A},$ $V_{GS} = -4.5\text{ V},$		6	8.5	nC
$Q_{gs}$	Gate-Source Charge			0.8		nC
$Q_{gd}$	Gate-Drain Charge			1.3		nC

### Drain-Source Diode Characteristics and Maximum Ratings

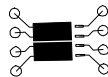
$I_S$	Maximum Continuous Drain-Source Diode Forward Current				-1.3	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -1.3\text{ A}$ (Note 2)		-0.78	-1.2	V

#### Notes:

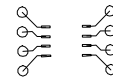
- 1:  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta JA}$  is determined by the user's board design.



a.  $78^\circ\text{C/W}$  on a  $0.5\text{ in}^2$  pad of 2oz copper.



b.  $125^\circ\text{C/W}$  on a  $0.02\text{ in}^2$  pad of 2oz copper.



c.  $135^\circ\text{C/W}$  on a  $0.003\text{ in}^2$  pad of 2oz copper.

Scale 1 : 1 on letter size paper

- 2: Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

Typical Characteristics

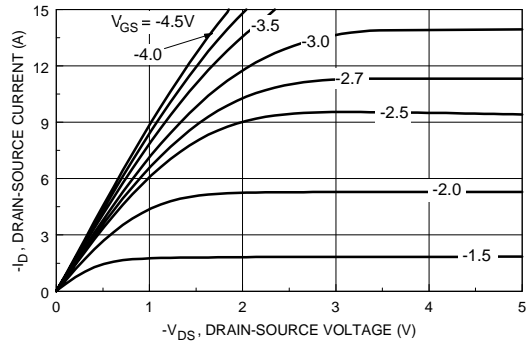


Figure 1. On-Region Characteristics.

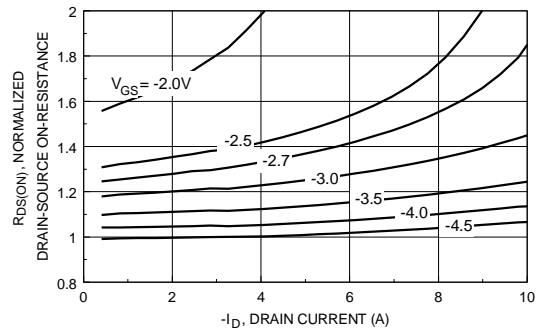


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

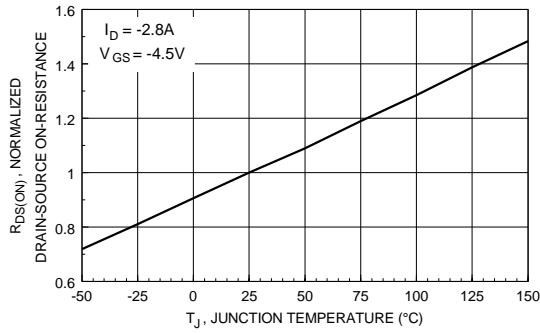


Figure 3. On-Resistance Variation with Temperature.

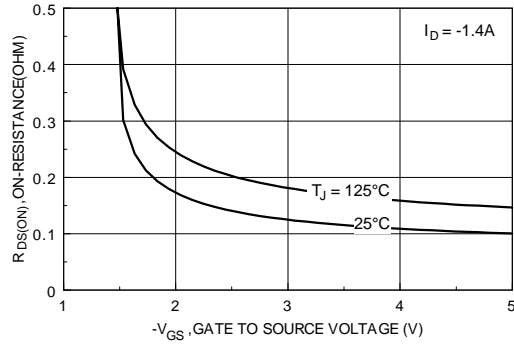


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

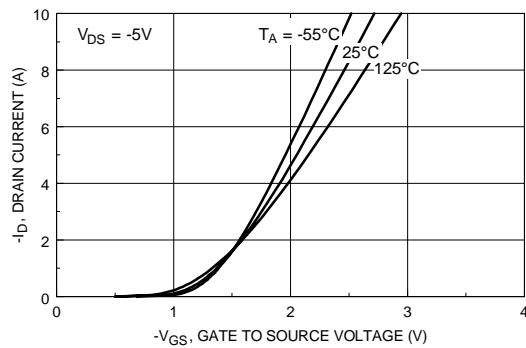


Figure 5. Transfer Characteristics.

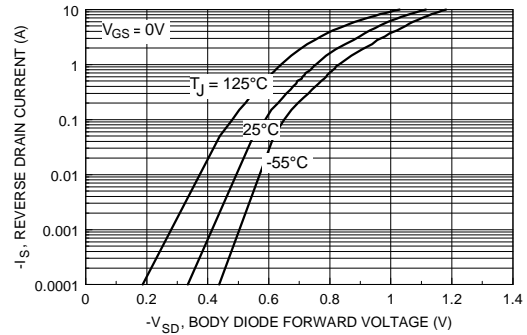


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)

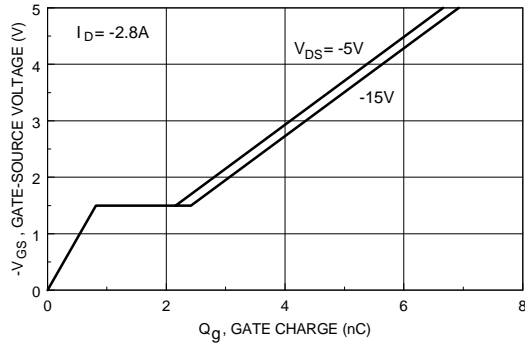


Figure 7. Gate-Charge Characteristics.

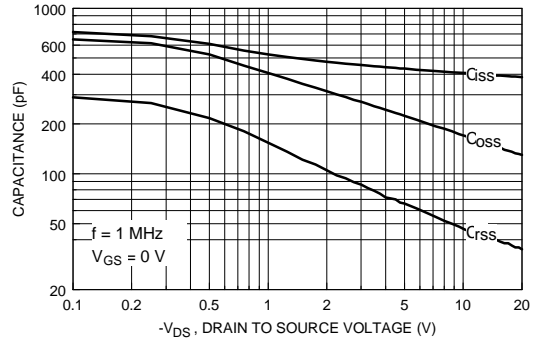


Figure 8. Capacitance Characteristics.

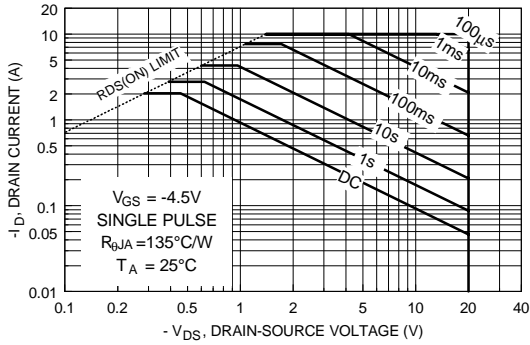


Figure 9. Maximum Safe Operating Area.

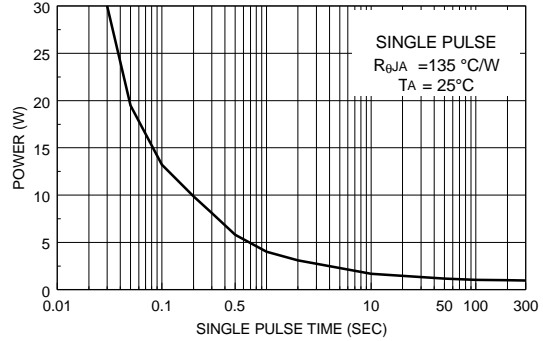


Figure 10. Single Pulse Maximum Power Dissipation.

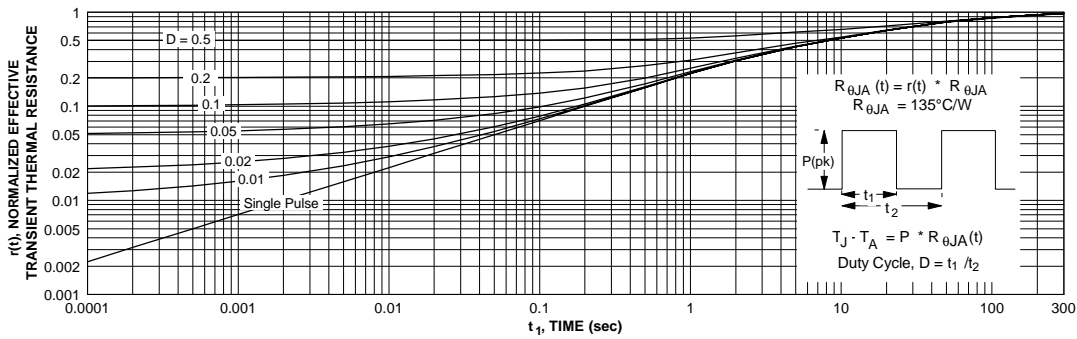


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1. Transient thermal response will change depending on the circuit board design.

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